CNZ2153 (ON2153)

Reflective Photosensor

For contactless SW and object detection

Overview

CNZ2153 is a photosensor detecting the change of reflective light in which a high efficiency GaAs infrared light emitting diode is used as the light emitting element, and a Si phototransistor is used as the light detecting element. The two elements are located parallel in the same direction and objects are detected when passing in front of the device.

■ Features

- Fast response
- Small size, light weight

Applications

- Detection of paper, film and cloth
- Optical mark reading
- Detection of coin and bill
- Detection of position and edge
- Start, end mark detection of magnetic tape

Absolute Maximum Ratings $T_a = 25^{\circ}C$

F	Symbol	Rating	Unit	
	Power dissipation *1	P_{D}	75	mW
Input (Light emitting diode)	Forward current	I_{F}	50	mA
	Reverse voltage	V _R	3	O V
Output (Photo transistor)	Collector-emitter voltage (Base open)	V _{CEO}	30	V
	Emitter-collector voltage (Base open)	V_{ECO}	10 5 HS	N. V.
	Collector current	I_{C}	20	mA
	Collector power dissipation *2	P _C	50	mW
Operating ambient temp	T _{opr}	-25 to +85	°C	
Storage temperature	T _{stg}	-30 to +100	% °C	

Note) *1: Input power derating ratio is 1.0 mW/°C at $T_a \ge 25$ °C

^{*2:} Output power derating ratio is 0.67 mW/°C at $T_a \ge 25$ °C

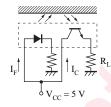
CNZ2153 Panasonic

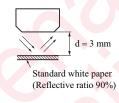
■ Electrical-Optical Characteristics $T_a = 25$ °C±3°C

	Parameter	Symbol	Conditions	Min	Тур	Max	Unit
Input characteristics	Reverse current	I_R	$V_R = 3 V$			10	μΑ
	Forward voltage	V _F	$I_F = 50 \text{ mA}$		1.2	1.5	V
	Terminal capacitance	C _t	$V_R = 0 V, f = 1 MHz$		50		pF
Output characteristics	Collector-emitter cutoff current (Base open)	I _{CEO}	$V_{CE} = 10 \text{ V}$			0.2	μА
Transfer characteristics	Collector current *1, *2	I_{C}	$V_{CC} = 5 \text{ V, } I_F = 20 \text{ mA,}$ $R_L = 100 \Omega$	100		1200	μА
	Collector-emitter saturation voltage	V _{CE(sat)}	$I_F = 50 \text{ mA}, I_C = 0.1 \text{ mA}$			0.5	V
	Rise time *3	t _r	$V_{CC} = 10 \text{ V}, I_C = 0.1 \text{ mA},$		6.0		μs
	Fall time *3	t_{f}	$R_L = 100 \Omega$		6.0		μs

Note) 1. Input and output are practiced by electricity.

- 2. This device is designed by disregarding radiation.
- 3. *1: Output current measurement circuit

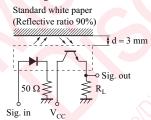




*2: Rank classification

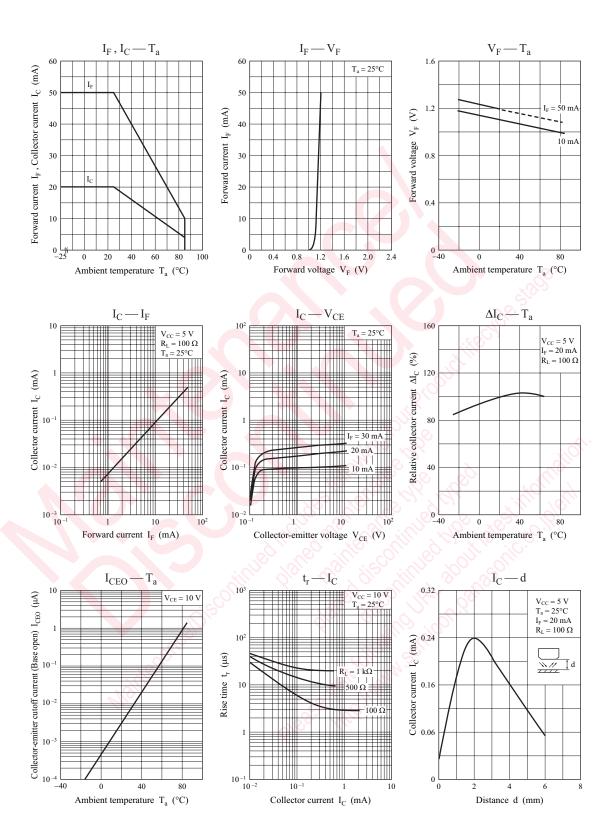
Rank	Q	R	S	No-rank
$I_{C}(\mu A)$	100 to 300	200 to 600	400 to 1200	100 to 1200

*3: Switching time measurement circuit



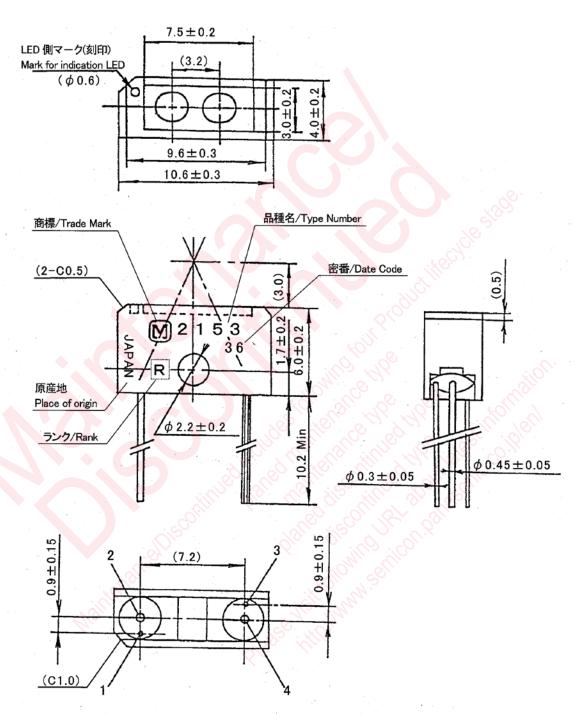


2 SHG00053CED



■ Package (Unit: mm)

LSSLRR4S0001



(注 1) 密番及びマークは、目視又は顕微鏡に於いて解読できる事。 (Note1) What a date code and mark sees an attention and can decode in a microscope.

- Pin name
 - 1: Cathode
 - 2: Anode
 - 3: Emitter
 - 4: Collector

4 SHG00053CED

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